Central™
Semiconductor Corp.

PROCESS CPD81

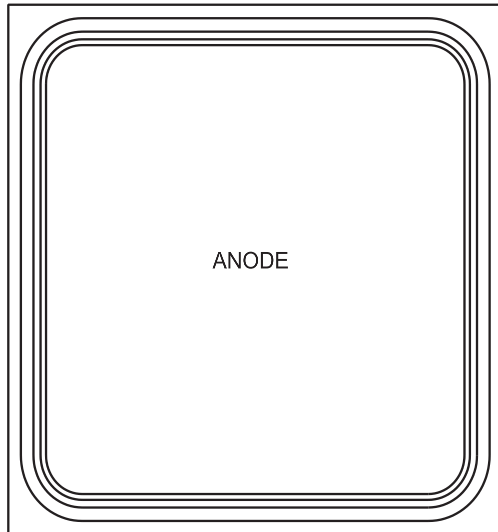
Schottky Rectifier

5 Amp Schottky Barrier Rectifier Chip

PROCESS DETAILS

Die Size	72.5 x 72.5 MILS
Die Thickness	11.8 MILS
Anode Bonding Pad Area	63.8 x 63.8 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER
2,178

PRINCIPAL DEVICE TYPES
CZSH5-40
CZSH10-40CN (Dual Chip)

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

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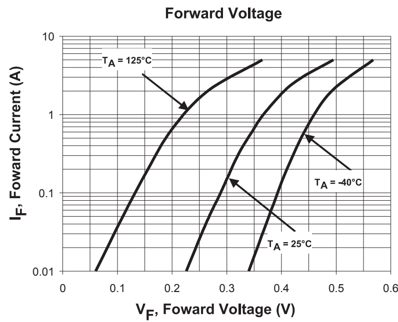
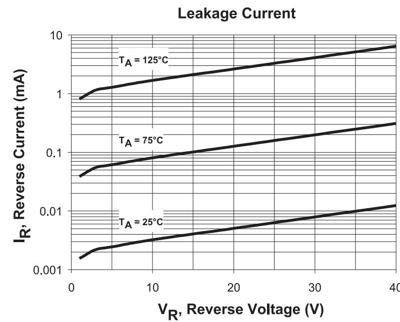
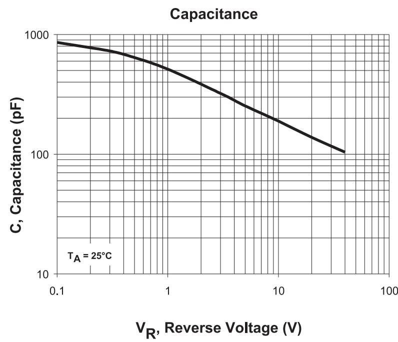
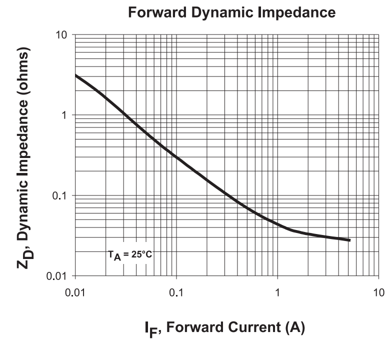
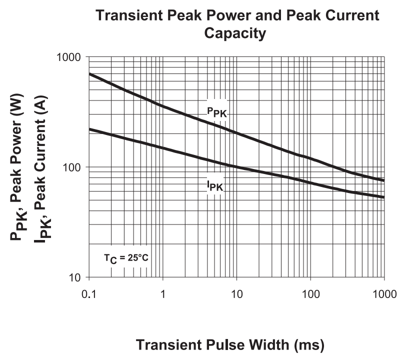
Typical Electrical Characteristics

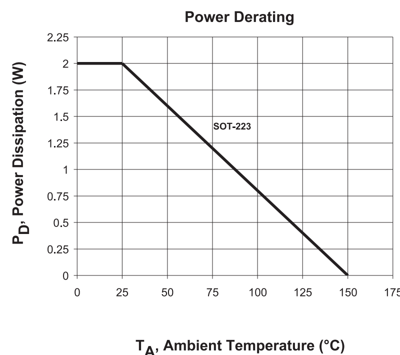












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